

## A B S T R A C T

## AN EDGE-EMITTING TUNABLE SEMICONDUCTOR LASER

5           The invention concerns a tunable edge-emitting  
semiconductor laser (10) including a resonant cavity  
delimited by two reflectors (15, 20), one of which is a  
fixed reflector (15) and the other of which is a mobile  
reflector (20), and including an active section (1) with  
10 gain of length  $L_1$  and a tunable section (2) of length  $L_2$ ,  
characterized in that the total length of the cavity  
 $L = L_1 + L_2$  is less than or equal to  $20 \mu\text{m}$ .

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35 Translation of the title and the abstract as they were when originally filed by the  
Applicant. No account has been taken of any changes that may have been made  
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38.2, and/or 48.3.